

Li, Jiapeng

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	A Timing Model for the Optimal Design of a Prototype Active-Matrix Display. IEEE Transactions on Electron Devices, 2020, 67, 3167-3174.	3.0	2
2	P4: Enhanced Scalability and Reliability of High Mobility Elevated-Metal Metal-Oxide Thin-Film Transistors with Bandgap Engineering. Digest of Technical Papers SID International Symposium, 2020, 51, 1322-1325.	0.3	1
3	242: Distinguished Student Paper: Fluorination for Enhancing the Resistance of Indium-Gallium-Zinc Oxide Thin-Film Transistor against Hydrogen-Induced Degradation. Digest of Technical Papers SID International Symposium, 2020, 51, 347-350.	0.3	3
4	Fluorinated indium-gallium-zinc oxide thin-film transistor with reduced vulnerability to hydrogen-induced degradation. Journal of the Society for Information Display, 2020, 28, 520-527.	2.1	10
5	Systematic Defect Manipulation in Metal Oxide Semiconductors towards High-Performance Thin-Film Transistors. , 2020, , .		0
6	Resilience of Fluorinated Indium-Gallium-Zinc Oxide Thin-Film Transistor Against Hydrogen-Induced Degradation. IEEE Electron Device Letters, 2020, 41, 729-732.	3.9	17
7	1.3: A Timing Model for the Design of an Active-Matrix Display. Digest of Technical Papers SID International Symposium, 2019, 50, 13-16.	0.3	1
8	8.2: <i>Invited Paper:</i> Elevated-Metal Metal-Oxide Thin-Film Transistor with Self-Aligned Source/Drain Regions. Digest of Technical Papers SID International Symposium, 2019, 50, 75-78.	0.3	0
9	P11: Carrier Concentration Reduction by Fluorine Doping in P-Type SnO Thin-Film Transistors. Digest of Technical Papers SID International Symposium, 2019, 50, 1251-1254.	0.3	2
10	Self-Aligned Elevated-Metal Metal-Oxide Thin-Film Transistors for Displays and Flexible Electronics. , 2019, , .		11
11	A Comparative Study on Fluorination and Oxidation of Indium-Gallium-Zinc Oxide Thin-Film Transistors. IEEE Electron Device Letters, 2018, 39, 196-199.	3.9	37
12	Fluorination-Enabled Monolithic Integration of Enhancement- and Depletion-Mode Indium-Gallium-Zinc Oxide TFTs. IEEE Electron Device Letters, 2018, 39, 692-695.	3.9	25
13	A Physical Model for Metal-Oxide Thin-Film Transistor Under Gate-Bias and Illumination Stress. IEEE Transactions on Electron Devices, 2018, 65, 142-149.	3.0	15
14	Three-Mask Elevated-Metal Metal-Oxide Thin-Film Transistor With Self-Aligned Definition of the Active Island. IEEE Electron Device Letters, 2018, 39, 35-38.	3.9	5
15	P1.5: Edge Effects of Three-Mask Elevated-Metal Metal-Oxide Thin-Film Transistor and Their Elimination. Digest of Technical Papers SID International Symposium, 2018, 49, 531-534.	0.3	1
16	8.1: <i>Invited Paper:</i> Enhanced Elevated-Metal Metal-Oxide Thin-Film Transistor Technology. Digest of Technical Papers SID International Symposium, 2018, 49, 75-78.	0.3	2
17	P1.4: Elevated-Metal Metal-Oxide Thin-Film Transistor with Fluorinated Indium-Gallium-Zinc Oxide Channel towards Flexible Applications. Digest of Technical Papers SID International Symposium, 2018, 49, 528-530.	0.3	0
18	24.3: Short-Channel Indium-Gallium-Zinc Oxide Thin-Film Transistor Enabled by Thermal Dehydrogenation and Oxidizing Defect-Suppression. Digest of Technical Papers SID International Symposium, 2018, 49, 255-258.	0.3	0

#	ARTICLE	IF	CITATIONS
19	A Bottom-Gate Metalâ€“Oxide Thin-Film Transistor With Self-Aligned Source/Drain Regions. IEEE Transactions on Electron Devices, 2018, 65, 2820-2826.	3.0	15
20	Pâ€“21: Threeâ€“Mask Elevatedâ€“Metal Metalâ€“Oxide Thinâ€“Film Transistor Technology for Highâ€“Resolution AMOLED Application. Digest of Technical Papers SID International Symposium, 2018, 49, 1256-1259.	0.3	0
21	Pâ€“15: The Use of Fluorination to Enhance the Performance and the Reliability of Elevatedâ€“Metal Metalâ€“Oxide Thinâ€“Film Transistors. Digest of Technical Papers SID International Symposium, 2018, 49, 1235-1238.	0.3	14
22	Characteristics of Elevated-Metal Metal-Oxide Thin-Film Transistors Based on Indium-Tin-Zinc Oxide. IEEE Electron Device Letters, 2017, 38, 894-897.	3.9	19
23	An oxidation-last annealing for enhancing the reliability of indium-gallium-zinc oxide thin-film transistors. Applied Physics Letters, 2017, 110, .	3.3	24
24	Elevated metal metal-oxide thin-film transistor â€” A new bottom-gate transistor architecture for flat-panel displays. , 2016, , .		0
25	High-performance and reliable elevated-metal metal-oxide thin-film transistor for high-resolution displays. , 2016, , .		33
26	Elevated-Metal Metal-Oxide (EMMO) Thin-Film Transistor: Technology and Characteristics. IEEE Electron Device Letters, 2016, , 1-1.	3.9	30
27	Thermally Induced Variation of the Turn-ON Voltage of an Indiumâ€“Galliumâ€“Zinc Oxide Thin-Film Transistor. IEEE Transactions on Electron Devices, 2015, 62, 3703-3708.	3.0	13
28	A Comparative Study on the Effects of Annealing on the Characteristics of Zinc Oxide Thin-Film Transistors With Gate-Stacks of Different Gas-Permeability. IEEE Electron Device Letters, 2014, 35, 841-843.	3.9	24